

Plastic Medium Power Bipolar Transistors

BD237G (NPN), BD234G (PNP)

Designed for use in 5.0 to 10 W audio amplifiers and drivers utilizing complementary or quasi complementary circuits.

Features

- High DC Current Gain
- Epoxy Meets UL 94 V0 @ 0.125 in
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

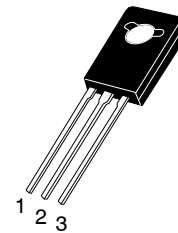
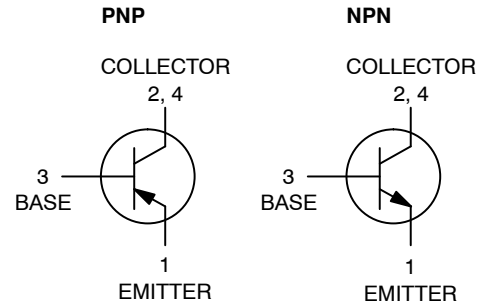
Rating	Symbol	Value	Unit
Collector-Emitter Voltage BD234G DB237G, BD238G	V_{CEO}	45 80	Vdc
Collector-Base Voltage BD234G DB237G, BD238G	V_{CBO}	60 100	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current	I_C	2.0	Adc
Base Current	I_B	1.0	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$	P_D	25	W
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
ESD - Human Body Model	HBM	3B	V
ESD - Machine Model	MM	C	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

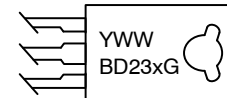
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	5.0	$^\circ\text{C}/\text{W}$

2.0 AMPERES POWER TRANSISTORS 25 WATTS



TO-225
CASE 77-09
STYLE 1

MARKING DIAGRAM



- Y = Year
- WW = Work Week
- BD23x = Device Code
x = 4, 7 or 8
- G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 4.

*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

BD237G (NPN), BD234G (PNP)

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Collector-Emitter Sustaining Voltage (Note 1) ($I_C = 0.1 \text{ Adc}$, $I_B = 0$) BD237G, BD238G BD234G	$V_{(BR)CEO}$	80 45	- -	Vdc
Collector Cutoff Current ($V_{CB} = 100 \text{ Vdc}$, $I_E = 0$) BD237G, BD238G ($V_{CB} = 60 \text{ Vdc}$, $I_E = 0$) BD234G	I_{CBO}	- -	0.1 0.1	mAdc
Emitter Cutoff Current ($V_{BE} = 5.0 \text{ Vdc}$, $I_C = 0$)	I_{EBO}	-	1.0	mAdc
DC Current Gain ($I_C = 0.15 \text{ A}$, $V_{CE} = 2.0 \text{ V}$) ($I_C = 1.0 \text{ A}$, $V_{CE} = 2.0 \text{ V}$)	h_{FE1} h_{FE2}	40 25	- -	-
Collector-Emitter Saturation Voltage (Note 1) ($I_C = 1.0 \text{ Adc}$, $I_B = 0.1 \text{ Adc}$)	$V_{CE(sat)}$	-	0.6	Vdc
Base-Emitter On Voltage (Note 1) ($I_C = 1.0 \text{ Adc}$, $V_{CE} = 2.0 \text{ Vdc}$)	$V_{BE(on)}$	-	1.3	Vdc
Current-Gain - Bandwidth Product ($I_C = 250 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ MHz}$)	f_T	3.0	-	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

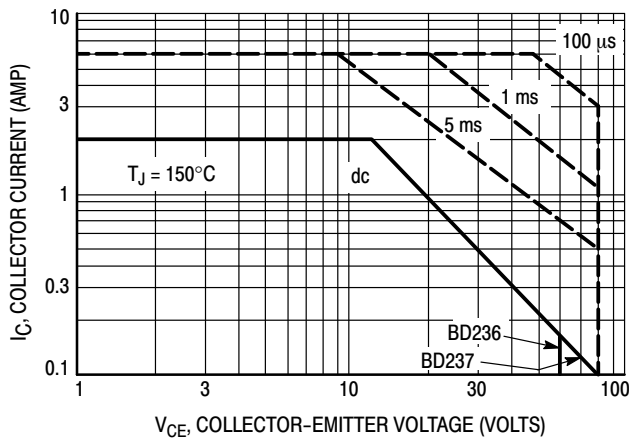


Figure 1. Active Region Safe Operating Area

The Safe Operating Area Curves indicate I_C - V_{CE} limits below which the device will not enter secondary breakdown. Collector load lines for specific circuits must fall within the applicable Safe Area to avoid causing a catastrophic failure. To insure operation below the maximum T_J , power-temperature derating must be observed for both steady state and pulse power conditions.

BD237G (NPN), BD234G (PNP)

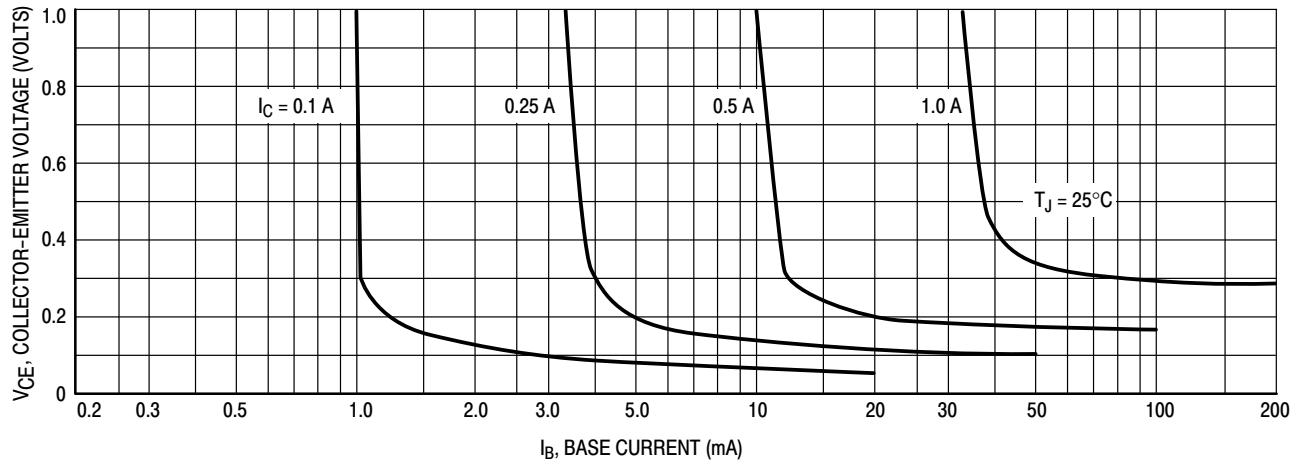


Figure 2. Collector Saturation Region

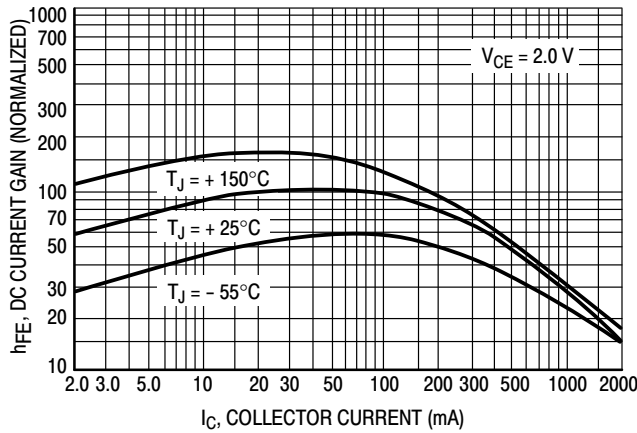


Figure 3. Current Gain

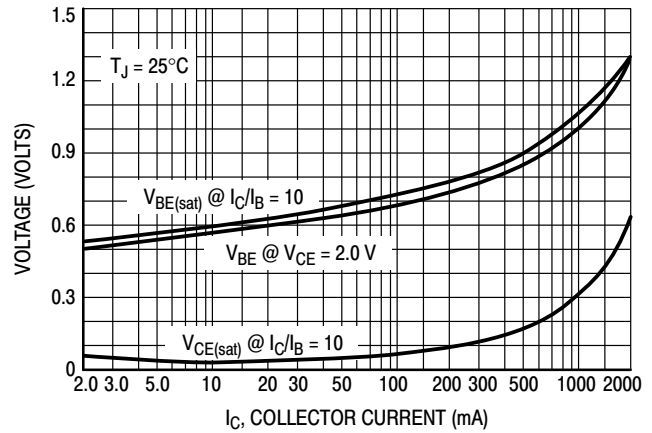


Figure 4. "On" Voltages

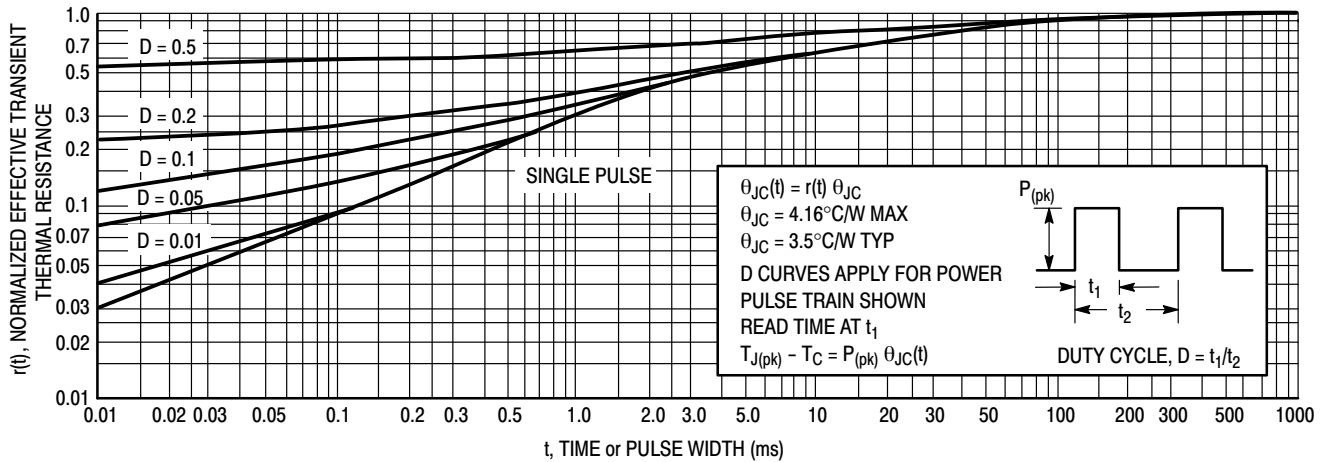


Figure 5. Thermal Response

BD237G (NPN), BD234G (PNP)

ORDERING INFORMATION

Device	Package	Shipping
BD237G	TO-225 (Pb-Free)	500 Units / Box

DISCONTINUED (Note 2)

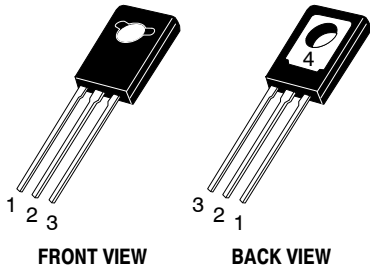
BD234G	TO-225 (Pb-Free)	500 Units / Box
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2. **DISCONTINUED:** These devices are not recommended for new design. Please contact your **onsemi** representative for information. The most current information on these devices may be available on www.onsemi.com.

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

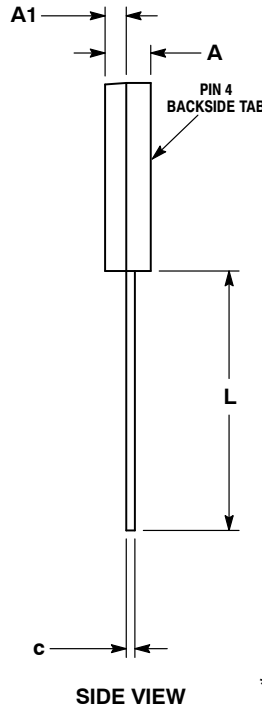
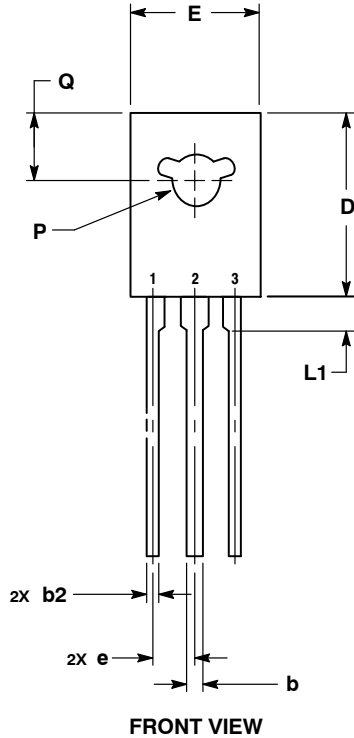
ON Semiconductor®



TO-225
CASE 77-09
ISSUE AD

DATE 25 MAR 2015

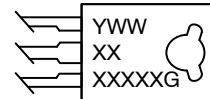
SCALE 1:1



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. NUMBER AND SHAPE OF LUGS OPTIONAL.

DIM	MILLIMETERS	
	MIN	MAX
A	2.40	3.00
A1	1.00	1.50
b	0.60	0.90
b2	0.51	0.88
c	0.39	0.63
D	10.60	11.10
E	7.40	7.80
e	2.04	2.54
L	14.50	16.63
L1	1.27	2.54
P	2.90	3.30
Q	3.80	4.20

GENERIC MARKING DIAGRAM*



- Y = Year
- WW = Work Week
- XXXXX = Device Code
- G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present.

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|---------------------------------------------------------------------|-----------------------------------------------------------------|---------------------------------------------------------------------|-------------------------------------------------------------------|-----------------------------------------------------------------|
| <p>STYLE 1:
PIN 1. EMITTER
2., 4. COLLECTOR
3. BASE</p> | <p>STYLE 2:
PIN 1. CATHODE
2., 4. ANODE
3. GATE</p> | <p>STYLE 3:
PIN 1. BASE
2., 4. COLLECTOR
3. EMITTER</p> | <p>STYLE 4:
PIN 1. ANODE 1
2., 4. ANODE 2
3. GATE</p> | <p>STYLE 5:
PIN 1. MT 1
2., 4. MT 2
3. GATE</p> |
| <p>STYLE 6:
PIN 1. CATHODE
2., 4. GATE
3. ANODE</p> | <p>STYLE 7:
PIN 1. MT 1
2., 4. GATE
3. MT 2</p> | <p>STYLE 8:
PIN 1. SOURCE
2., 4. GATE
3. DRAIN</p> | <p>STYLE 9:
PIN 1. GATE
2., 4. DRAIN
3. SOURCE</p> | <p>STYLE 10:
PIN 1. SOURCE
2., 4. DRAIN
3. GATE</p> |

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